

## 2SK1762

### Silicon N Channel MOS FET

REJ03G0969-0200  
(Previous: ADE-208-1316)  
Rev.2.00  
Sep 07, 2005

#### Application

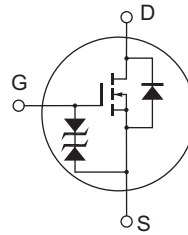
High speed power switching

#### Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator, DC-DC converter

#### Outline

RENESAS Package code: PRSS0003AD-A  
(Package name: TO-220FM)



1. Gate
2. Drain
3. Source

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	250	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	12	A
Drain peak current	I <sub>D(pulse)</sub> * <sup>1</sup>	48	A
Body to drain diode reverse drain current	I <sub>DR</sub>	12	A
Channel dissipation	P <sub>ch</sub> * <sup>2</sup>	35	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1 %  
 2. Value at T<sub>c</sub> = 25°C

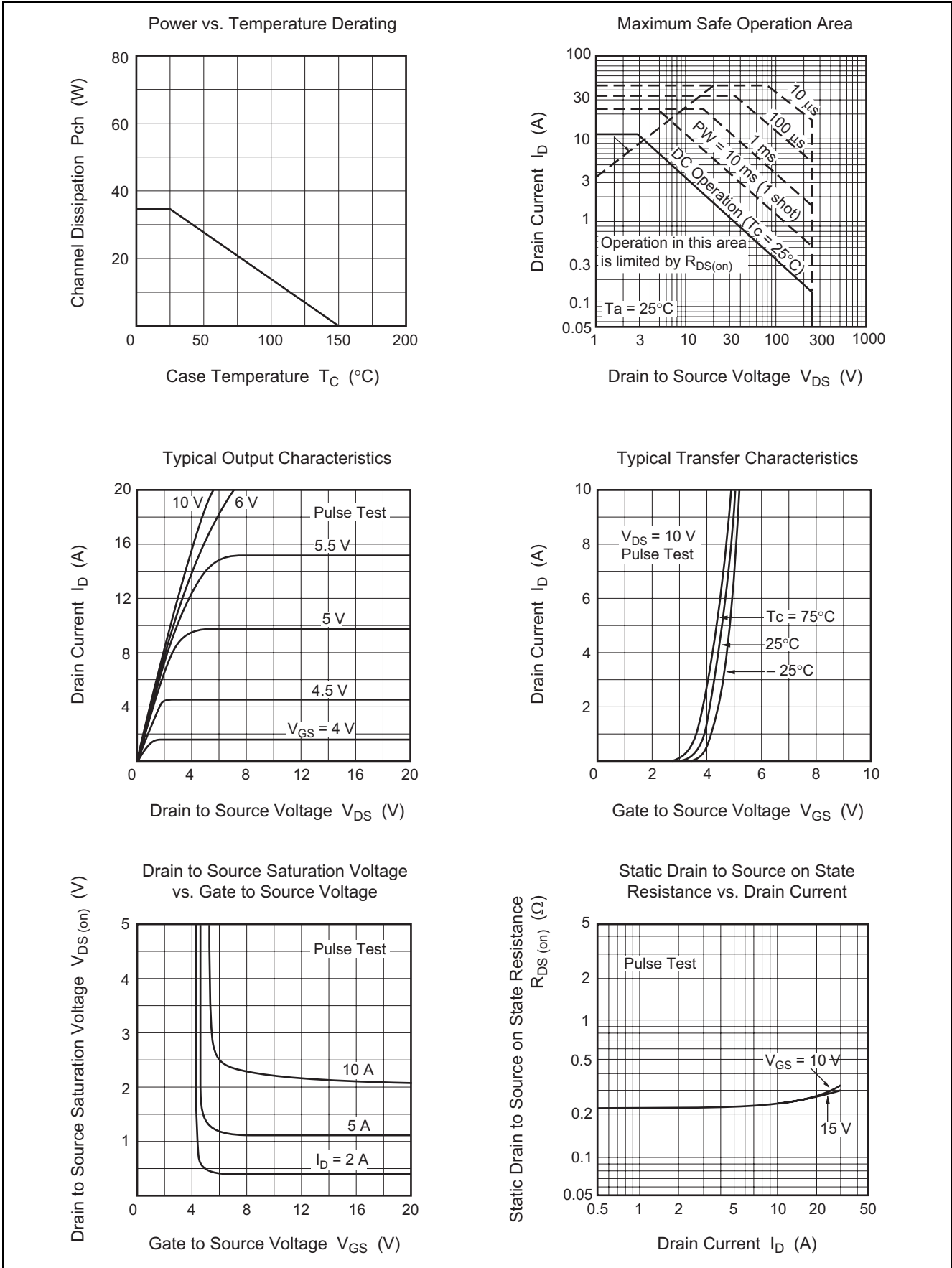
## Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	250	—	—	V	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0
Gate to source breakdown voltage	V <sub>(BR)GSS</sub>	±30	—	—	V	I <sub>G</sub> = ±100 μA, V <sub>DS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±25 V, V <sub>DS</sub> = 0
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	250	μA	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0
Gate to source cutoff voltage	V <sub>GS(off)</sub>	2.0	—	3.0	V	I <sub>D</sub> = 1 mA, V <sub>DS</sub> = 10 V
Static drain to source on state resistance	R <sub>DS(on)</sub>	—	0.23	0.35	Ω	I <sub>D</sub> = 6 A, V <sub>GS</sub> = 10 V* <sup>3</sup>
Forward transfer admittance	y <sub>fs</sub>	5.0	8.0	—	S	I <sub>D</sub> = 6 A, V <sub>DS</sub> = 10 V* <sup>3</sup>
Input capacitance	C <sub>iss</sub>	—	1100	—	pF	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0, f = 1 MHz
Output capacitance	C <sub>oss</sub>	—	440	—	pF	
Reverse transfer capacitance	C <sub>rss</sub>	—	68	—	pF	
Turn-on delay time	t <sub>d(on)</sub>	—	20	—	ns	I <sub>D</sub> = 6 A, V <sub>GS</sub> = 10 V, R <sub>L</sub> = 5 Ω
Rise time	t <sub>r</sub>	—	65	—	ns	
Turn-off delay time	t <sub>d(off)</sub>	—	100	—	ns	
Fall time	t <sub>f</sub>	—	44	—	ns	
Body to drain diode forward voltage	V <sub>DF</sub>	—	1.0	—	V	I <sub>F</sub> = 12 A, V <sub>GS</sub> = 0
Body to drain diode reverse recovery time	t <sub>rr</sub>	—	200	—	ns	I <sub>F</sub> = 12 A, V <sub>GS</sub> = 0, di <sub>F</sub> /dt = 100 A/μs

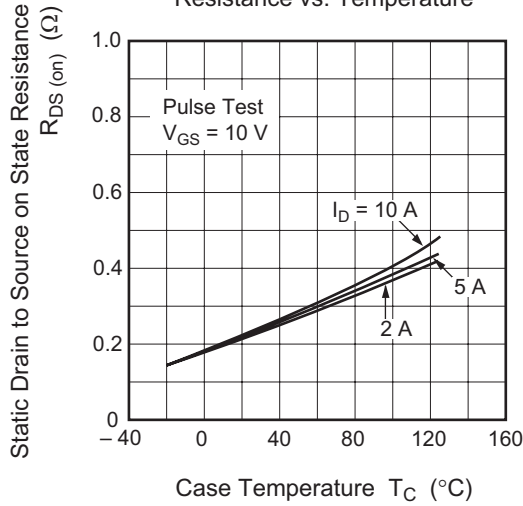
Note: 3. Pulse Test

主要特性 (Main Characteristics)

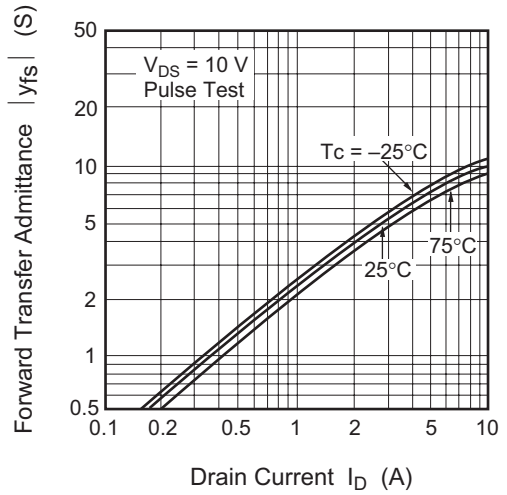


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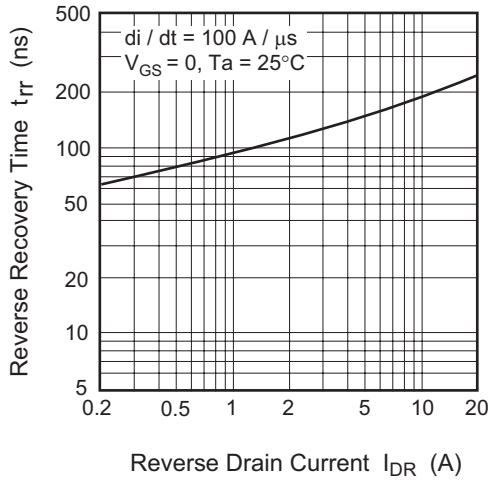
Static Drain to Source on State Resistance vs. Temperature



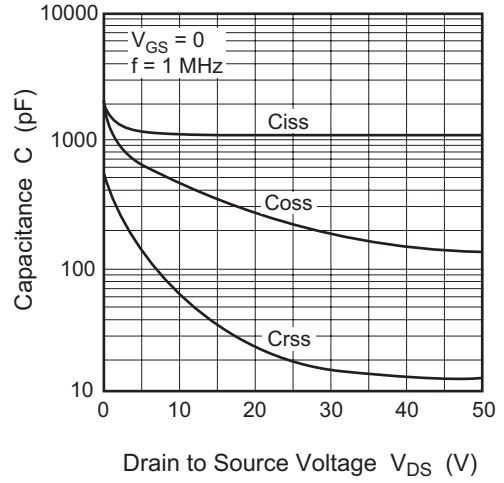
Forward Transfer Admittance vs. Drain Current



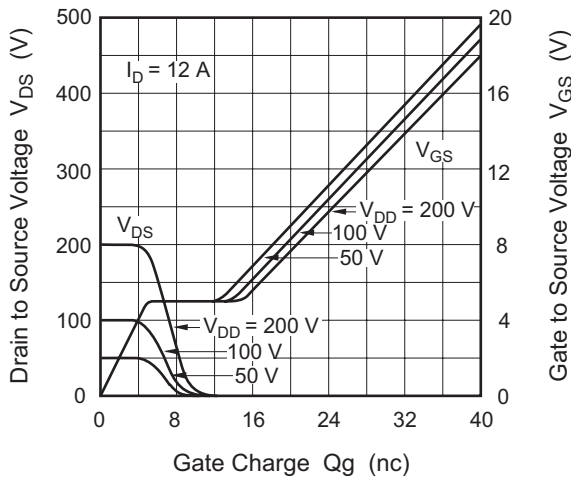
Body to Drain Diode Reverse Recovery Time



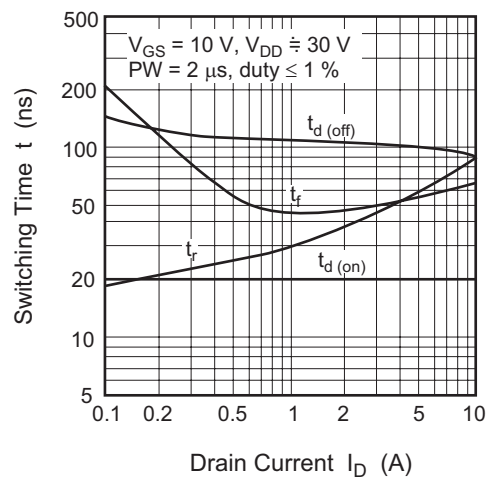
Typical Capacitance vs. Drain to Source Voltage



Dynamic Input Characteristics

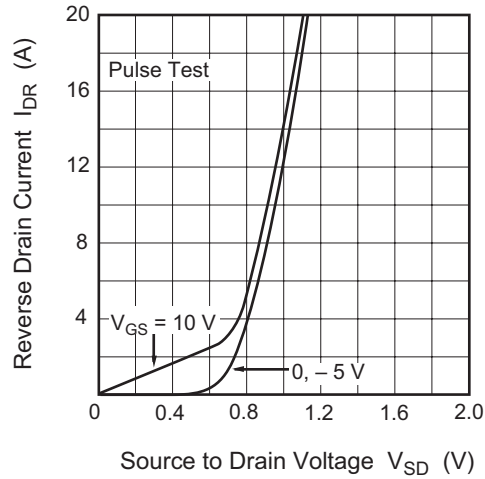


Switching Characteristics

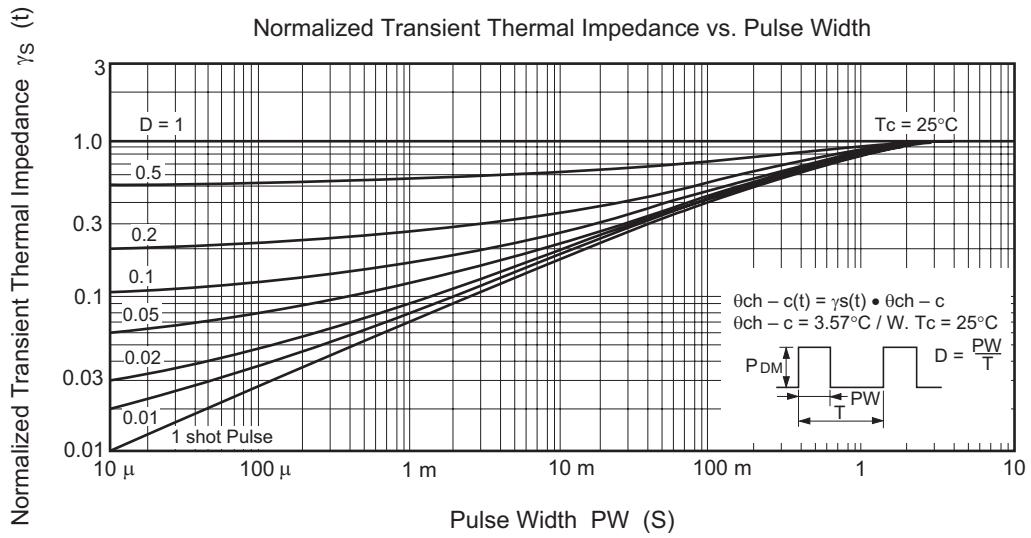


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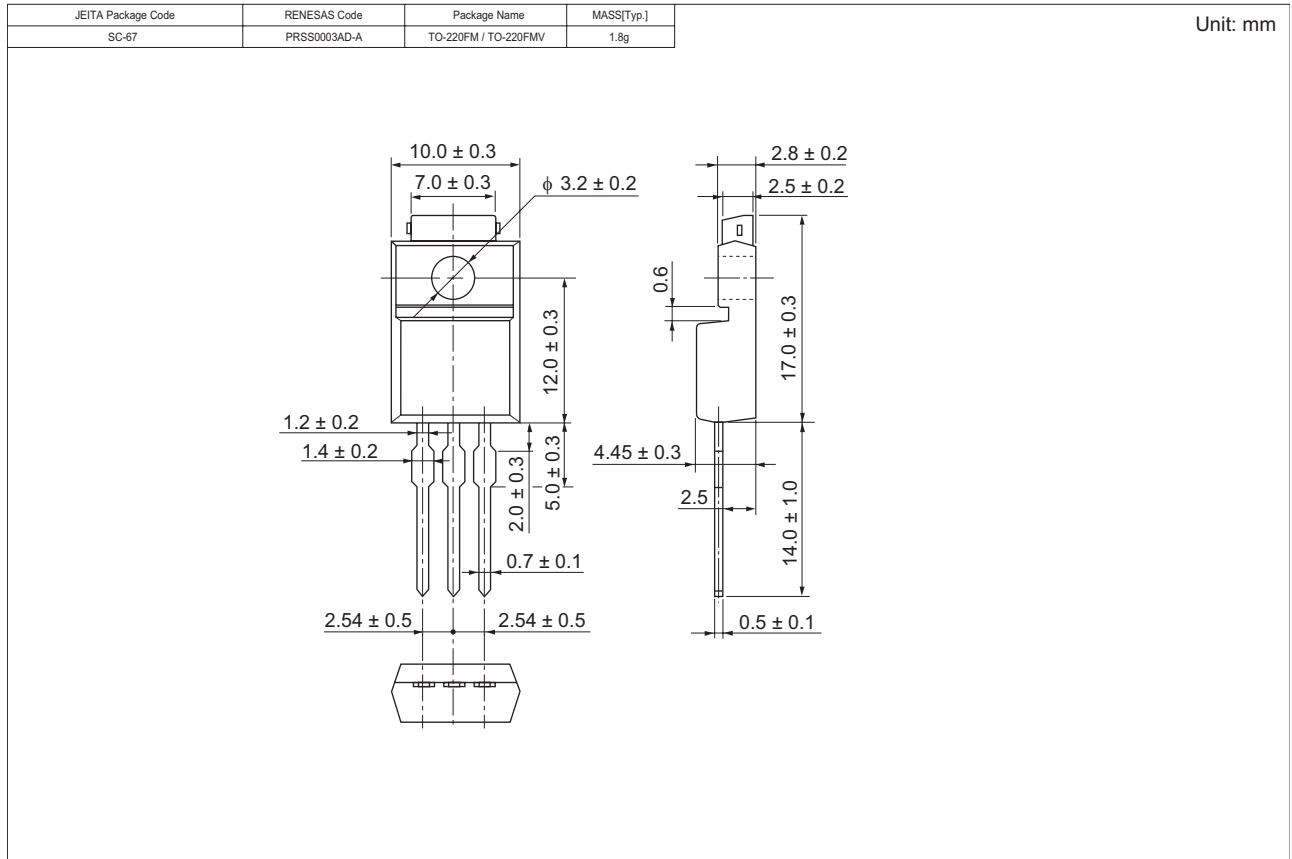
Reverse Drain Current vs. Source to Drain Voltage



Normalized Transient Thermal Impedance vs. Pulse Width



2SK1762 Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK1762-E	500 pcs	Box (Sack)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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